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Contents

Proceedings of 17th International Conference on Crystal Growth and Epitaxy (ICCGE-17)

Chairpersons' preface	1
Guest Editors' Preface P. Gille, W. Miller, K. Sangwal and E. Talik	4
Jan Czochralski: Brief sketch of his life and achievements A. Pajaczkowska	5
The historical development of the Czochralski method R. Uecker	7
Fundamentals and modelling of growth processes	
Ab initio studies of early stages of nitride growth process on silicon carbide M. Sznajder, E. Wachowicz and J.A. Majewski	25
Density functional study of GaN(0001)/AlN(0001) high electron mobility transistor structures J. Sołtys, M. Ptasińska, J. Piechota and S. Krukowski	30
Structure of hydrated calcium carbonates: A first-principles study R. Demichelis, P. Raiteri and J.D. Gale	33
Molecular dynamics simulations of organic crystal dissolution: The lifetime and stability of the polymorphic forms of para-amino benzoic acid in aqueous environment D. Toroz, R.B. Hammond, K.J. Roberts, S. Harris and T. Ridley	38
Formation of regular polyicosahedral and defected crystalline structures in growing Lennard-Jones clusters W. Polak	44
Modeling the nucleation statistics in vapor–liquid–solid nanowires N.V. Sibirev, M.V. Nazarenko, D.A. Zeze and V.G. Dubrovskii	51
Crystal nucleation kinetics of polyethylene on active centers Z. Kožíšek, M. Hikosaka, K. Okada and P. Demo	56
Effect of nucleation on chirality conversion induced by random fluctuation H. Katsuno and M. Uwaha	59
Nucleation and growth of fluoride crystals by agglomeration of the nanoparticles P.P. Fedorov, V.V. Osiko, S.V. Kuznetsov, O.V. Uvarov, M.N. Mayakova, D.S. Yasirkina, A.A. Ovsyannikova, V.V. Voronov and V.K. Ivanov	63
Analyzing capture zone distributions (CZD) in growth: Theory and applications T.L. Einstein, A. Pimpinelli and D. Luis González	67
Pinning of steps near equilibrium without impurities, adsorbates, or dislocations N. Akutsu	72
Adsorption of gallium on GaN(0001) surface in ammonia-rich conditions: A new effect associated with the Fermi level position P. Kempisty, P. Strak, K. Sakowski and S. Krukowski	78
Kinetics of crystal growth of vivianite, $\text{Fe}_3(\text{PO}_4)_2 \cdot 8\text{H}_2\text{O}$, from solution at 25, 35 and 45 °C H.E. Lundager Madsen and H.C. Bruun Hansen	82

Ordering of Brownian particles from walls due to an external force M. Sato, H. Katsuno and Y. Suzuki	87
Global steady state solutions for lamellar eutectic growth in directional solidification J.-J. Xu, X.-M. Li and Y.-Q. Chen	93
Global instabilities of lamellar eutectic growth in directional solidification J.-J. Xu, Y.-Q. Chen and X.-M. Li	99
The phenomenon of "cold plume" instability in Czochralski hydrodynamic model: Physical and numerical simulation V.S. Berdnikov, A.I. Prostomolotov and N.A. Verezub	106
Simplified numerical approach for estimation of effective segregation coefficient at the melt/crystal interface A.I. Prostomolotov, N.A. Verezub and A.E. Voloshin	111
The effect of the shear flow on particle growth in the undercooled melt M. Chen, X. Ji, X. Xu, Y. Zheng, P. Qian and Z. Wang	116
Hydrodynamical aspects of the floating zone silicon crystal growth process K. Surovovs, A. Muiznieks, A. Sabanskis and J. Virbulis	120
Experimental study of the structural characteristics of Al melts on the basis of Fourier analysis of acoustic emission signals V. Vorontsov, D. Zhuravlev and A. Cherepanov	124
Numerical design of induction heating in the PVT growth of SiC crystal J. Su, X. Chen and Y. Li	128
Bulk crystal growth	
Crystal growth of 50 cm square mono-like Si by directional solidification and its characterization Y. Miyamura, H. Harada, K. Jiptner, J. Chen, R.R. Prakash, S. Nakano, B. Gao, K. Kakimoto and T. Sekiguchi	133
Numerical study of silicon crystal ridge growth G. Barinovs, A. Sabanskis and A. Muiznieks	137
Germanium-doped crystalline silicon: Effects of germanium doping on boron-related defects X. Zhu, X. Yu and D. Yang	141
Vertical Bridgman growth of sapphire crystals, with thin-neck formation process K. Hoshikawa, T. Taishi, E. Ohba, C. Miyagawa, T. Kobayashi, J. Yanagisawa and M. Shinozuka	146
Modified Bridgman growth and properties of mid-infrared LiInSe_2 crystal S. Wang, X. Zhang, X. Zhang, C. Li, Z. Gao, Q. Lu and X. Tao	150
Growth of CdWO_4 crystals by the low thermal gradient Czochralski technique and the properties of a (010) cleaved surface E.N. Galashov, V.V. Atuchin, A.S. Kozhukhov, L.D. Pokrovsky and V.N. Shlegel	156
Crystal growth and characterization of 4 in. $\text{YCa}_4\text{O}(\text{BO}_3)_3$ crystal X. Tu, Y. Zheng, K. Xiong, Y. Shi and E. Shi	160
4inch langasite crystals grown along SAW-cut orientations X. Tu, Y. Zheng, K. Xiong, Y. Shi and E. Shi	164
Crystal growth and neutron diffraction studies of Li_xCoO_2 bulk single crystals S. Uthayakumar, M.S. Pandiyan, D.G. Porter, M.J. Gutmann, R. Fan and J.P. Goff	169
Growth of Al doped $\text{Ca}_3\text{TaGa}_3\text{Si}_2\text{O}_{14}$ piezoelectric single crystals with various Al concentrations T. Kudo, Y. Yokota, M. Sato, K. Tota, K. Onodera, S. Kurosawa, K. Kamada and A. Yoshikawa	173

Growth and EPR properties of HoVO ₄ single crystals G. Leniec, S.M. Kaczmarek, M. Berkowski, M. Główacki, T. Skibiński, A. Suchocki and Y.A. Zhydachevskii	177
Growth problems, thermal expansion and scintillation properties of Ce:Li ₆ Lu(BO ₃) ₃ crystals under thermal neutron excitation S. Pan, Z. Fu, D. Sun, G. Ren and Y. Heng	181
Investigation on the Li, Ba//BO ₂ , F ternary reciprocal system and growth of bulk β-BaB ₂ O ₄ crystals E.A. Simonova, N.G. Kononova, V.S. Shevchenko and A.E. Kokh	185
Study on rapid growth of 98% deuterated potassium dihydrogen phosphate (DKDP) crystals L. Zhang, G. Yu, H. Zhou, L. Li, M. Xu, B. Liu, S. Ji, L. Zhu, F. Liu and X. Sun	190
Bulk single crystals of ammonium acid phthalate grown by the Sankaranarayanan–Ramasamy method for optical limiting applications A. Arunkumar and P. Ramasamy	195
Investigation on the SR method growth, etching, birefringence, laser damage threshold and thermal characterization of strontium bis (hydrogen L-malate) hexahydrate single crystal A. Senthil and P. Ramasamy	200
Investigations on synthesis, growth and physical characterization of lithium selenoindate single crystals P. Vijayakumar, M. Magesh, A. Arunkumar, G.A. Babu, P. Ramasamy and K.G.M. Nair	205
Structural, FTIR, thermal and dielectric studies of gel grown manganese–copper mixed levo tartrate crystals S.J. Joshi, K.P. Tank, P.M. Vyas and M.J. Joshi	210
Organic/inorganic-doped aromatic derivative crystals: Growth and properties F. Stanculescu, I. Ionita and A. Stanculescu	215
Biological and biogenic crystallization	
Growth and characterization of struvite-Na crystals C.K. Chauhan and M.J. Joshi	221
Towards a better understanding of the nucleation behavior of α and γ polymorphs of glycine from aqueous solution in the presence of selective additives by charge compensation mechanism K. Renuka Devi and K. Srinivasan	227
Cyclic growth and dissolution of camphor crystals in quinary, ternary, and binary solutions: A study on crystal behavior in storm glass T. Mitsuya, K. Takahashi and K. Nagashima	233
Crystal distortion of monoclinic hen egg-white lysozyme crystals using X-ray digital topography K. Wako, D. Fujii, S. Tsukashima, T. Kishi, M. Tachibana and K. Kojima	238
Crystal growth of cholesterol in hydrogels and its characterization J. Manuel Bravo-Arredondo, A. Moreno and M.E. Mendoza	242
Industrial crystallization	
Nucleation control and separation of paracetamol polymorphs through swift cooling crystallization process C. Sudha and K. Srinivasan	248
Studies on the effect of different operational parameters on the crystallization kinetics of α -lactose monohydrate single crystals in aqueous solution P. Parimaladevi and K. Srinivasan	252
Controlling of morphology and polymorph of calcium oxalate crystals by using polyelectrolytes E. Akyol and M. Öner	260

The effect of ultrasonication on calcium carbonate crystallization in the presence of biopolymer S. Kirkboga, M. Oner and E. Akyol	266
Effect of sample volume on the metastable zone width of potassium nitrate aqueous solutions E. Mielińczek-Brzóska	271
Redox process catalysed by growing crystal—strengeite, $\text{FePO}_4 \cdot 2\text{H}_2\text{O}$, crystallizing from solution with iron(II) and hydroxylamine H.E. Lundager Madsen	275
Formation of ZnO rods with varying diameters from $\epsilon\text{-Zn(OH)}_2$ J. Wang and L. Xiang	279
Global simulations of heat transfer in directional solidification of multi-crystalline silicon ingots under a traveling magnetic field Q. Yu, L. Liu, Z. Li and P. Su	285
Numerical investigation of the effect of a crucible cover on crystal growth in the industrial directional solidification process for silicon ingots Z. Li, Y. Zhang, Z. Hu, G. Zhou and L. Liu	291
Quality evaluation of multi-crystalline silicon ingots produced in a directional solidification furnace with different theories W. Zhao, L. Liu, L. Sun and A. Geng	296
Characterization	
Low-frequency noise in diagnostics of power blue InGaN/GaN LEDs A.E. Chernyakov, M.E. Levenshtein, N.A. Talnishnikh, E.I. Shabunina and N.M. Shmidt	302
Emission spectra and thermoluminescence of rare-earth-doped bismuth silicate crystals grown by modified Bridgman method Z. Xiong, J. Xu, Y. Zhang, Z. Tan, H. Shen, B. Yang, Y. Li, J. Chen and J. Guo	305
Strain evolution during the growth of epitaxial Ge layers between narrow oxide trenches B. Kim, S.-W. Kim, H. Jang, J.-H. Kim, S. Koo, D.-H. Kim, B.-G. Min, S.-J. Park, J.S. Song and D.-H. Ko	308
Application of microwave spectroscopy to studies of electron transport properties A. Wolos and A. Drabinska	314
Defect analyses of selective epitaxial grown GaAs on STI patterned (001) Si substrates S.W. Kim, Y.D. Cho, C.S. Shin, W.K. Park, D.H. Kim and D.H. Ko	319
Synthesis, growth, structural, optical and thermal properties of a new organic salt crystal: 3-nitroanilinium trichloroacetate E. Selvakumar, A. Chandramohan, G. Anandha Babu and P. Ramasamy	323
Precise lattice parameter measurements of $\text{Sr}_{0.72}\text{Ba}_{0.25}\text{Nb}_2\text{O}_{5.97}$ single crystals R. Paszkowski, K.B. Wokulska, J. Dec and T. Łukasiewicz	327
Polarized Raman spectra in $\beta\text{-Ga}_2\text{O}_3$ single crystals T. Onuma, S. Fujioka, T. Yamaguchi, Y. Itoh, M. Higashiwaki, K. Sasaki, T. Masui and T. Honda	330
Synthesis, crystal structure, characterization and luminescent properties of $\text{KBaTbB}_2\text{O}_6$ Z. Lian, J. Sun, Z. Ma, L. Zhang, D. Shen, G. Shen, X. Wang and Q. Yan	334
Magnetism and superconductivity in Sb-doped binary and ternary iron chalcogenide single crystals D. Cherian, G.M. Nagendra and S. Elizabeth	338
Growth of Eu:SrI ₂ bulk crystals and their scintillation properties Y. Yokota, S. Kurosawa, K. Nishimoto, K. Kamada and A. Yoshikawa	343

Modelling of X-ray diffraction curves for GaN nanowires on Si(111)	
V.P. Kladko, A.V. Kuchuk, H.V. Stanchu, N.V. Safriuk, A.E. Belyaev, A. Wierzbicka, M. Sobanska, K. Klosek and Z.R. Zytkiewicz	347
Characterization of $(\text{Bi}_{0.5}\text{Na}_{0.5})_{1-x}\text{Ba}_x\text{TiO}_3$ grown by the TSSG method	
M. Woll, M. Burianek, D. Klimm, S. Gorfman and M. Mühlberg	351
Measurements of strain in AlGaN/GaN HEMT structures grown by plasma assisted molecular beam epitaxy	
J. Borysiuk, K. Sobczak, A. Wierzbicka, E. Jezierska, K. Klosek, M. Sobanska, Z.R. Zytkiewicz and B. Lucznik	355
In situ monitoring, new equipment and technologies	
In situ observation of melting and crystallization of Si on porous Si_3N_4 substrate that repels Si melt	
H. Itoh, H. Okamura, S. Asanoma, K. Ikemura, M. Nakayama and R. Komatsu	359
Calculations of parameters of RHEED oscillations using different models of the scattering potential	
Z. Mitura	364
Control of crystallinity of GaN grown on sapphire substrate by metalorganic vapor phase epitaxy using <i>in situ</i> X-ray diffraction monitoring method	
M. Iwaya, T. Yamamoto, D. Tanaka, D. Iida, S. Kamiyama, T. Takeuchi and I. Akasaki	367
Quantitative monitoring of InAs quantum dot growth using X-ray diffraction	
Masamitu. Takahasi	372
In situ diagnostics of the SiC nanostructures growth process	
A. Dałbrowska, A. Bzymek and A. Huczko	376
Electronic processes in adatom dynamics at epitaxial semiconductor surfaces studied using MBE-STM combined system	
K. Kanisawa	381
Defect formation/elimination	
Morphology and formation mechanism of metallic inclusions in VB-grown sapphire crystals	
T. Taishi, T. Kobayashi, M. Shinozuka, E. Ohba, C. Miyagawa and K. Hoshikawa	388
Polytypism in SiC: Theory and experiment	
A. Lebedev and Y. Tairov	392
Segregation, precipitation and dislocation generation between seeds in directionally solidified mono-like silicon for photovoltaic applications	
M.G. Tsoutsouva, V.A. Oliveira, D. Camel, T.N. Tran Thi, J. Baruchel, B. Marie and T.A. Lafford	397
Experimental study of grain boundary orientations in multi-crystalline silicon	
T. Duffar, C.T. Nwosu, I.M. Asuo, J. Muzy, N.D.Q. Chau, Y. Du Terrail-Couvat and F. Robaut	404
Behavior of defects in α -plane GaN films grown by low-angle-incidence microchannel epitaxy (LAIMCE)	
N. Kuwano, Y. Ryu, M. Mitsuhasha, C.-H. Lin, S. Uchiyama, T. Maruyama, Y. Suzuki and S. Naritsuka	409
Structure, frequency dependent dielectric properties and domain configuration of PMN-PFN-PT single crystal	
N. Luo, Q. Li, Q. Yan, Y. Zhang, Z. Xia and X. Chu	414
The subgrain structure in turbine blade roots of CMSX-4 superalloy	
W. Bogdanowicz, R. Albrecht, J. Sieniawski and K. Kubiāk	418
Synchrotron topography studies of the operation of double-ended Frank-Read partial dislocation sources in 4H-SiC	
H. Wang, F. Wu, S. Byrappa, B. Raghothamachar, M. Dudley, P. Wu, I. Zwieback, A. Souzis, G. Ruland and T. Anderson	423

Nanomaterials and low-dimensional structures

Diffusion-induced growth of nanowires: Generalized boundary conditions and self-consistent kinetic equation V.G. Dubrovskii and Yu.Yu. Hervieu	431
Molecular beam epitaxial growth of GaSb/GaAs quantum dots on Ge substrates M. Kunrugsa, S. Kiravittaya, S. Sopitpan, S. Ratanathammaphan and S. Panyakeow	441
Combustion synthesis of Si-related crystalline nanostructures M. Soszyński, O. Łabędź and A. Huczko	445
Organic luminophor metal complex in inorganic glass matrix—A new hybrid material R. I. Avetisov, O. Petrova, A. Khomyakov, O. Mushkalo, A. Akkuzina, A. Cherednichenko and I. Avetisov	449
Red fluorescence in LaF ₃ : Nd ³⁺ , Sm ³⁺ nanocrystals grown by rapid microwave assisted synthesis: A comparative analysis of vibrational, thermal and electrical properties M.M. Khandpekar and S.G. Gaurkhede	453
Synthesis of C ₇₀ two-dimensional nanosheets by liquid–liquid interfacial precipitation method K. Osonoe, R. Kano, K. Miyazawa and M. Tachibana	458
Structural and morphologic characterization of zirconia–silica nanocomposites prepared by a modified sol–gel method M. Stoia, P. Barvinschi and F. Barvinschi	462
Self-propagating high-temperature synthesis (SHS) of crystalline nanomaterials A. Huczko, M. Kurcz, A. Dąbrowska, P. Baranowski, A. Bhattacharai and S. Gierlotka	469
Pure and zinc doped nano-hydroxyapatite: Synthesis, characterization, antimicrobial and hemolytic studies K.P. Tank, K.S. Chudasama, V.S. Thaker and M.J. Joshi	474
Investigations of YF ₃ ; 1% Er nanocrystals A. Skuta, E. Talik, L. Lipińska, M. Michalska, A. Guzik and P. Zajdel	480
Effects of La, Gd, or Lu co-doping on crystal growth and scintillation properties of Eu:SrI ₂ single crystals K. Nishimoto, Y. Yokota, S. Kurosawa, J. Pejchal, K. Kamada, V. Chani and A. Yoshikawa	484
Crystalline nanostructures of heavy metal iodides L. Fornaro, I. Aguiar, M.P. Barthaburu, A. Olivera, I. Galain and M. Mombrú	489
Forming two-dimensional structure of DNA-functionalized Au nanoparticles via lipid diffusion in supported lipid bilayers T. Isogai, A. Piednoir, E. Akada, Y. Akahoshi, R. Tero, S. Harada, T. Ujihara and M. Tagawa	494
MBE grown microcavities based on selenium and tellurium compounds J.-G. Rousset, J. Kobak, E. Janik, T. Jakubczyk, R. Rudniewski, P. Piotrowski, M. Ściesiek, J. Borysiuk, T. Slupinski, A. Golnik, P. Kossacki, M. Nawrocki and W. Pacuski	499
Surfaces and interfaces	
Cluster diffusion on two-dimensional surface with immobile impurities H. Katsuno and M. Sato	504
Contact angle of sapphire melt and bubble generation on crucible material T. Suzuki, K. Shirotsuki, T. Taishi and K. Hoshikawa	508
4H-SiC surface structure transitions during crystal growth following bunching in a fast sublimation process F. Krzyżewski	511
Adsorption of ammonia on hydrogen covered GaN(0001) surface – Density Functional Theory study P. Kempisty, P. Strak, K. Sakowski and S. Krukowski	514

Effects of TMSb overpressure on InSb surface morphology for InSb epitaxial growth using low pressure metalorganic chemical vapor deposition S. Park, J. Jung, C. Seok, K.W. Shin, S. Hyun Park, Y. Nanishi, Y. Park and E. Yoon	518
Thin films and epitaxial growth	
Low temperature amorphous silicon carbide thin film formation process on aluminum surface using monomethyl-silane gas and trichlorosilane gas H. Habuka, M. Tsuji and A. Hirooka	523
Structural and optical characterization of AlGaN/GaN layers M. Jayasakthi, R. Ramesh, P. Arivazhagan, R. Loganathan, K. Prabakaran, M. Balaji and K. Baskar	527
Development of scintillating screens based on the single crystalline films of Ce doped $(\text{Gd}, \text{Y})_3(\text{Al}, \text{Ga}, \text{Sc})_5\text{O}_{12}$ multi-component garnets Y. Zorenko, V. Gorbenko, V. Savchyn, T. Zorenko, A. Fedorov and O. Sidletskiy	532
Rare earth doped LiYF_4 single crystalline films grown by liquid phase epitaxy for the fabrication of planar waveguide lasers F. Starecki, W. Bolaños, G. Brasse, A. Benayad, M. Morales, J.-L. Doualan, A. Braud, R. Moncorgé and P. Camy	537
The influence of pressure on growth of 3C-SiC heteroepitaxial layers on silicon substrates D. Teklinska, K. Grodecki, I. Jozwik-Biała, P. Caban, A. Olszyna and W. Strupinski	542
High-temperature growth and characterization of $(\text{Er}, \text{Yb}): \text{YAl}_3(\text{BO}_3)_4$ and $\text{NdAl}_3(\text{BO}_3)_4$ epitaxial layers E. Volkova, V. Maltsev, O. Kolganova and N.I. Leonyuk	547
Influence of CdS deposition technique for CdS/CdTe solar cells applications S. Rubio, J.L. Plaza and E. Diéguez	550
Growth of high quality micrometer scale GaAs/Si crystals from (001) Si nano-areas in SiO_2 C. Renard, N. Cherkashin, A. Jaffre, T. Molière, G. Hallais, L. Vincent, J. Alvarez, D. Mencaraglia, A. Michel and D. Bouchier	554
Photoluminescence study of the strain relaxation of GaAs crystals grown on deeply patterned Si substrates A. Scaccabarozzi, S. Bietti, A. Fedorov, H. von Känel, L. Miglio and S. Sanguinetti	559
Selective growth of (001) GaAs using a patterned graphene mask Y. Hirota, Y. Shirai, H. Iha, Y. Kito, M. Suzuki, H. Kato, N. Yamamoto, T. Maruyama and S. Naritsuka	563
Spectroscopic characterization of high-purity polycrystalline Bi–Te films grown by thermal evaporation R. Rapacz, K. Balin, A. Nowak and J. Szade	567
Microstructural analysis and optical characteristics of Cu-doped ZnO thin films prepared by DC magnetron sputtering B. Allabergenov, O. Tursunkulov, A.I. Abidov, B. Choi, J.S. Wook and S. Kim	573
Growth and luminescent properties of Ce and Ce–Tb doped $(\text{Y}, \text{Lu}, \text{Gd})_2\text{SiO}_5:\text{Ce}$ single crystalline films Y. Zorenko, V. Gorbenko, V. Savchyn, T. Zorenko, B. Grinyov, O. Sidletskiy and A. Fedorov	577
Study on Ag modified TiO_2 thin films grown by sputtering deposition using sintered target A. Abidov, B. Allabergenov, J. Lee, C. Gómez-Solís, I. Juárez-Ramírez and S. Kim	584
Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films S. Fujita and K. Kaneko	588
Intermetallic and highly correlated electronic materials	
Floating zone crystal growth of Lu_2PdSi_3 silicide C. Cao, C.G.F. Blum and W. Löser	593

The effect of process parameters on floating zone crystal growth of selected cuprates N. Wizent, N. Leps, G. Behr, R. Klingeler, B. Büchner and W. Löser	596
Single crystal growth of the ErPd_2Si_2 intermetallic compound C. Cao, R. Klingeler, N. Leps, G. Behr and W. Löser	601
Preparation of $\text{NdMn}_{1-x}\text{Fe}_x\text{O}_{3+\delta}$ single crystals—Effect of preparation atmosphere and iron doping M. Mihalik, S. Mat'aš, M. Vavra, J. Briančin, M. Mihalik, M. Fitta, V. Kavečanský and J. Kopeček	605
Single crystal growth and structural characterization of iron telluride doped with chromium and zinc I.I. Kruk and P. Zajdel	608
Single crystal growth in the Ga–Pd system J. Schwerin, D. Müller, S. Kiese and P. Gille	613
Effect of annealing on spinodally decomposed Co_2CrAl grown via floating zone technique A. Omar, C.G.F. Blum, W. Löser, B. Büchner and S. Wurmehl	617
Single crystal growth of the intermetallic compound InPd M. Hahne and P. Gille	622
Crystal growth of intermetallic clathrates: Floating zone process and ultra rapid crystallization A. Prokofiev, X. Yan, M. Ikeda, S. Löffler and S. Paschen	627
Materials for spintronics	
Electric-field effects on magnetic properties of molecular beam epitaxially grown thin (Ga,Mn)Sb layers H.W. Chang, S. Akita, F. Matsukura and H. Ohno	633
Growth, characterization and study of ferromagnetism of bismuth telluride doped with manganese I.V. Fedorchenco, S.F. Marenkin, A. Avdonin, V. Domukhovski, W. Dobrowolski, J. Heikinheimo, E. Korhonen and F. Tuomisto	636
The impact of position of Mn δ -doping on the formation of CdTe/ZnTe quantum dots with single magnetic ions K. Gietka, J. Kobak, E. Janik, J.G. Rousset, J. Borysiuk, M. Nawrocki, A. Golnik, P. Kossacki and W. Pacuski	640
Photoluminescence studies of giant Zeeman effect in MBE-grown cobalt-based dilute magnetic semiconductors M. Papaj, J. Kobak, J.G. Rousset, E. Janik, M. Nawrocki, P. Kossacki, A. Golnik and W. Pacuski	644
Wide bandgap semiconductors	
Growth of GaN films on circle array patterned Si (111) substrates K.-L. Lin, B.T. Tran, C.-C. Chung and E.-Y. Chang	648
Doping effects in InN/GaN short-period quantum well structures—Theoretical studies based on density functional methods P. Strak, P. Kempisty, K. Sakowski and S. Krukowski	652
Arrangement of GaN nanowires grown by plasma-assisted molecular beam epitaxy on silicon substrates with amorphous Al_2O_3 buffers M. Sobanska, A. Wierzbicka, K. Klosek, J. Borysiuk, G. Tchutchulashvili, S. Gieraltowska and Z.R. Zytkiewicz	657
Investigation of TMIn pulse duration effect on the properties of InAlN/GaN heterostructures grown on sapphire by pulsed metal organic chemical vapor deposition J. Xue, J. Zhang and Y. Hao	661
Structural properties of Si-doped $\beta\text{-Ga}_2\text{O}_3$ layers grown by MOVPE D. Gogova, G. Wagner, M. Baldini, M. Schmidbauer, K. Irmscher, R. Schewski, Z. Galazka, M. Albrecht and R. Fornari	665

Growth of corundum-structured $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ alloy thin films on sapphire substrates with buffer layers N. Suzuki, K. Kaneko and S. Fujita	670
Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle K. Masumoto, K. Tamura, C. Kudou, J. Nishio, S. Ito, K. Kojima, T. Ohno and H. Okumura	673
Growth of SiC by PVT method with different sources for doping by a cerium impurity, CeO_2 or CeSi_2 K. Racka, E. Tymicki, K. Grasza, R. Jakieła, M. Pisarek, B. Surma, A. Avdonin, P. Skupiński and J. Krupka	677
Growth rate and surface morphology of 4H-SiC crystals grown from Si-Cr-C and Si-Cr-Al-C solutions under various temperature gradient conditions T. Mitani, N. Komatsu, T. Takahashi, T. Kato, K. Fujii, T. Ujihara, Y. Matsumoto, K. Kurashige and H. Okumura	681
Compound semiconductors	
Nonstoichiometry and luminescent properties of ZnSe crystals grown from melt and vapor I. Avetissov, K. Chang, N. Zhavoronkov, A. Davydov, E. Mozhevitsina, A. Khomyakov, S. Kobeleva and S. Neustroev	686
Studies on structural and optical properties of ZnSe and ZnSSe single crystals grown by CVT method P. Kannappan and R. Dhanasekaran	691
Growth, structure and magnetic properties of ZnCr_2Se_4 -single crystals doped by dysprosium I. Jendrzejewska, P. Zajdel, E. Maciążek and M. Sozańska	697
VGF growth of GaAs utilizing heater-magnet module C. Frank-Rotsch, N. Dropka, A. Glacki and U. Juda	702
Chemical vapor transport of chalcopyrite semiconductors: CuGaS_2 and AgGaS_2 R. Lauck, M. Cardona, R.K. Kremer, G. Siegle, J.S. Bhosale, A.K. Ramdas, H. Alawadhi, I. Miotkowski, A.H. Romero, A. Muñoz and A. Burger	708
Strain effect for different phosphorus content of InGaAs/GaAsP super-lattice in GaAs p-i-n single junction solar cell K. Watanabe, Y. Wang, H. Sodabanlu, M. Sugiyama and Y. Nakano	712
Si/Ge for microelectronics and photovoltaics	
Grain growth of cast-multicrystalline silicon grown from small randomly oriented seed crystal R.R. Prakash, T. Sekiguchi, K. Jiptner, Y. Miyamura, J. Chen, H. Harada and K. Kakimoto	717
Effects of crucible coating on the quality of multicrystalline silicon grown by a Bridgman technique V. Pupazan, R. Negrić, O. Bunoiu, I. Nicoara and D. Vizman	720
Improvement of multi-crystalline silicon ingot growth by using diffusion barriers C.C. Hsieh, A. Lan, C. Hsu and C.W. Lan	727
Impurities, inclusions, and dislocations in multicrystalline silicon grown from well-mixed and poorly mixed melts C. Funke, E. Schmid, G. Gärtner, S. Reißenweber, W. Fütterer, A. Poklad, L. Raabe, O. Pätzold and M. Stelter	732
Crystal growth of MCZ silicon with ultralow carbon concentration Y. Nagai, S. Nakagawa and K. Kashima	737
Three-dimensional phase field modeling of silicon thin-film growth during directional solidification: Facet formation and grain competition H.K. Lin and C.W. Lan	740
Growth of spherical Si crystals on porous Si_3N_4 substrate that repels Si melt H. Itoh, H. Okamura, C. Nakamura, T. Abe, M. Nakayama and R. Komatsu	748

Growth of silicon germanium by liquid phase diffusion with applied electric field N. Armour and S. Dost	753
Uniaxially strained SiGe(111) and SiGe(100) grown on selectively ion-implanted substrates K. Sawano, Y. Hoshi, S. Kubo, S. Yamada, K. Nakagawa and Y. Shiraki	758
$\text{Si}_{1-x}\text{Ge}_x$ ($x \geq 0.2$) crystal growth in the absence of a crucible A.C. Wagner, A. Cröll, M.A. Gonik, H. Hillebrecht, S. Binetti and A. LeDonne	762
The low thermal gradient CZ technique as a way of growing of dislocation-free germanium crystals V.A. Moskovskikh, P.V. Kasimkin, V.N. Shlegel, Y.V. Vasiliev, V.A. Gridchin and O.I. Podkopaev	767
Oxides and halides including materials for laser and nonlinear optical applications	
KNbO ₃ plate crystal grown by micro-pulling-down method from stoichiometric melt R. Komatsu, N. Masuda, M. Ueda and H. Itoh	772
Floating-zone growth and characterization of Ca _x Ba _{1-x} Nb ₂ O ₆ crystals Y. Ma, Y. Wang, Y. Jiang, H. Xu and G. Liu	777
Bulk growth of ZnGeP ₂ crystals and their study by X-ray topography G.A. Verozubova, A.O. Okunev and A.I. Griben'yukov	782
Flux growth and characterization of lead-free Sodium Bismuth Titanate–Barium Titanate single crystals K. Aravindh, G. Anandha Babu and P. Ramasamy	787
Composite boron nitride neutron detectors M. Roth, E. Mojaev, O. Khakhan, A. Fleider, E. Dul'kin and M. Schieber	791
Crystal growth of Bi ₂ TeO ₅ by a double crucible Czochralski method J.F. Carvalho, Z.V. Fabris, I. de Oliveira and J. Frejlich	795
Temperature dependence of PL and EPR spectra of Sr _{0.33} Ba _{0.67} Nb ₂ O ₆ :Cr (0.02 mol%) single crystals S.M. Kaczmarek, T. Tsuboi, A. Leniec, Y. Nakai, G. Leniec, M. Berkowski and W. Huang	798
Magnetic and optical properties of Co-doped PbMoO ₄ single crystals T. Skibiński, S.M. Kaczmarek, G. Leniec, T. Tsuboi, Y. Nakai, M. Berkowski, Z. Kowalski and W. Huang	802
Crystal growth of CW diode-pumped (Er ³⁺ , Yb ³⁺):GdAl ₃ (BO ₃) ₄ laser material V.V. Maltsev, E.V. Koporulina, N.I. Leonyuk, K.N. Gorbachenya, V.E. Kisel, A.S. Yasukevich and N.V. Kuleshov	807
Three-dimensional numerical simulation of flow, thermal and oxygen distributions for a Czochralski silicon growth with in a transverse magnetic field J.-C. Chen, P.-Y. Chiang, C.-H. Chang, Y.-Y. Teng, C.-C. Huang, C.-H. Chen and C.-C. Liu	813
Growth and high temperature properties of Ca ₃ Ta(Al _{0.9} Ga _{0.1}) ₃ Si ₂ O ₁₄ crystals with ordered langasite structure K. Xiong, Y. Zheng, X. Tu, S. Zhang, H. Kong and E. Shi	820
Defects in flux grown KBe ₂ BO ₃ F ₂ crystals L. Liu, T. Xu, X. Wang, X. Wang and C. Chen	824
Magnetic and optical properties of Cr/Mn-co-doped Li _{1.72} Na _{0.28} Ge ₄ O ₉ single crystals S.M. Kaczmarek, T. Tsuboi, A. Leniec, Y. Nakai, G. Leniec, M. Berkowski and W. Huang	828
Crystal growth and scintillation properties of selected fluoride crystals for VUV scintillators J. Pejchal, K. Fukuda, A. Yamaji, Y. Yokota, S. Kurosawa, R. Kral, M. Nikl and A. Yoshikawa	833
Phase formation and densification peculiarities of Y ₃ Al ₅ O ₁₂ :Nd ³⁺ during reactive sintering R.P. Yavetskiy, V.N. Baumer, A.G. Doroshenko, Y.L. Kopylov, D.Yu. Kosyanov, V.B. Kravchenko, S.V. Parkhomenko and A.V. Tolmachev	839

Czochralski growth and characterization of MgAl_2O_4 single crystals A.L. Bajor, M. Chmielewski, R. Diduszko, J. Kisielewski, T. Lukasiewicz, K. Orlinski, M. Romaniec and W. Szyrski	844
Novel materials and structures	
Ceramic material $\text{ZnSe}(\text{Te})$ fabricated by nanopowder technology: Fabrication, phase transformations and photoluminescence N.N. Kolesnikov, E.B. Borisenko, D.N. Borisenko, I.I. Zverkova, A.N. Tereshchenko, A.V. Timonina, I.B. Gnesin and V.K. Gartman	849
Properties of Li_2MoO_4 single crystals grown by Czochralski technique O. Barinova, S. Kirsanova, A. Sadovskiy and I. Avetissov	853
New chemical analogs of triglycine sulfate V.V. Ghazaryan, M. Fleck and A.M. Petrosyan	857
New mixed salts of L-histidinium(2+) comprising hexafluorosilicate anion A.M. Petrosyan, M. Fleck and V.V. Ghazaryan	863
Influence of a parallel electric field on the dispersion relation of graphene – A new route to Dirac logics S. Krukowski, J. Sołtys, J. Borysiuk and J. Piechota	869
The effect of hippuric acid on crystal growth, structural and optical properties of ZTS single crystals A. Kumaresh, R.A. Kumar, M. Arivanandhan and Y. Hayakawa	874
Improved chemical vapor transport growth of transition metal dichalcogenides A. Ubaldini and E. Giannini	878
Growth under external fields and microgravity	
Directional solidification of silicon under the influence of travelling magnetic field M. Cablea, K. Zaidat, A. Gagnoud, A. Nouri and Y. Delannoy	883
Numerical simulation of oxygen transport during the Czochralski silicon crystal growth with a cusp magnetic field J.-C. Chen, P.-C. Guo, C.-H. Chang, Y.-Y. Teng, C. Hsu, H.-M. Wang and C.-C. Liu	888
Influence of the Richardson number on EM force driven flow structures in square-shaped crucible V. Geza, B. Nacke, E. Baake and A. Jakovics	895
Czochralski growth of $\text{NaNO}_3\text{--LiNO}_3$ solid solution single crystals using axial vibrational control technique I. Avetissov, A. Sadovskiy, S. Belov, C. Kong Khan, E. Mozhevitsina, E. Sukhanova and E. Zharikov	899
Colloidal crystallization on tilted substrates under gravitational fields Y. Suzuki, A. Mori, M. Sato, H. Katsuno and T. Sawada	905
Report on the Meetings of the International Organization for Crystal Growth Executive Committee, Council and General Assembly held during ICCGE-17 in Warsaw (Poland) 11–16 August 2013 K. Kakimoto	910